

AMENDMENTS TO THE CLAIMS

1. (previously presented) A method for forming LED, comprising the steps of:
forming an LED epitaxial layer on a provisional substrate;
etching said LED epitaxial layer to form LED chips;
forming a reflecting layer on said LED chips;
forming a metal layer on said reflecting layer;
removing said provisional substrate to expose surfaces of said LED chips;
forming pads on said surfaces of said LED chips; and
separating said metal layer to form individual LED chips by means of
mechanical force.
2. (original) The method in claim 1, wherein a material of said reflecting layer is
Ag, Al, Rh, Pt, Pd, Ni, Ti, Co, Au, or the combination thereof.
3. (original) The method in claim 1, wherein said metal layer is formed by means
of electroplating, electroless plating, chemical vapor deposition, or the
combination thereof.
4. (original) The method in claim 1, wherein said metal layer is formed by means
of a physical vapor deposition.
5. (original) The method in claim 4, wherein said physical vapor deposition is
evaporation, sputtering deposition, or the combination thereof.
6. (original) The method in claim 1, wherein said provisional substrate is removed
by means of polishing, etching, laser ablation, or the combination thereof.
7. (original) The method in claim 1, wherein a material of said metal layer is Cu,
Al, Ni, Mo, W, Ag, Au, Ti, Co, Pd, Pt, Fe, or the combination thereof.

8. (original) The method in claim 1, wherein a thickness of said metal layer is more than 30 μ m.
9. (original) The method in claim 1, wherein a thickness of said metal layer between said every two LED chips is 5-30 μ m.
10. – 17. (canceled)